

Diode current

A silicon p-n junction diode is doped $N_A = 2E+15 \text{ cm}^{-3}$ and $N_D = 2E+17 \text{ cm}^{-3}$. At the temperature of operation $n_i = 1 \times 10^{10} \text{ cm}^{-3}$. The cross-sectional area of the diode is 10^{-4} cm^2 . The diffusion constants and recombination times are: $D_n = 20 \text{ cm}^2/\text{s}$, $D_p = 10 \text{ cm}^2/\text{s}$, $\tau_n = 7 \times 10^{-7} \text{ s}$, and $\tau_p = 5 \times 10^{-7} \text{ s}$.

What is the reverse saturation current of this diode?

Solution:

At first, we calculate the diffusion length for the holes and the electrons:

$$L_h = \sqrt{D_h \cdot \tau_h}$$

$$L_h = \sqrt{10 \frac{\text{cm}^2}{\text{s}} \cdot 5 \cdot 10^{-7} \text{ s}} = 2,236 \cdot 10^{-3} \text{ cm}$$

$$L_e = \sqrt{D_e \cdot \tau_e}$$

$$L_e = \sqrt{20 \frac{\text{cm}^2}{\text{s}} \cdot 7 \cdot 10^{-7} \text{ s}} = 3,742 \cdot 10^{-3} \text{ cm}$$

The current in a pn-diode consist only of diffusion current (all other currents are negligible), so we can calculate the current density with the known formula:

$$J_s = \left(\frac{e \cdot D_e}{L_e} \cdot n_0 + \frac{e \cdot D_h}{L_h} \cdot p_0 \right) = \left(\frac{e \cdot D_e}{L_e} \cdot \frac{n_i^2}{N_D} + \frac{e \cdot D_h}{L_h} \cdot \frac{n_i^2}{N_A} \right)$$

$$J_s = \left(\frac{1,602 \cdot 10^{-19} \text{ As} \cdot 20 \frac{\text{cm}^2}{\text{s}}}{3,742 \cdot 10^{-3} \text{ cm}} \cdot \frac{(1 \cdot 10^{10} \text{ cm}^{-3})^2}{2 \cdot 10^{17} \text{ cm}^{-3}} + \frac{1,602 \cdot 10^{-19} \text{ As} \cdot 10 \frac{\text{cm}^2}{\text{s}}}{2,236 \cdot 10^{-3} \text{ cm}} \cdot \frac{(1 \cdot 10^{10} \text{ cm}^{-3})^2}{2 \cdot 10^{15} \text{ cm}^{-3}} \right)$$

The current density is

$$J_s = 3,65 \cdot 10^{-11} \frac{\text{A}}{\text{cm}^2}.$$

To get the current, we have to multiply the current density with the cross-sectional area.

$$I_s = J_s \cdot A = 3,625 \cdot 10^{-11} \frac{\text{A}}{\text{cm}^2} \cdot 10^{-4} \text{ cm}^2$$

The reverse saturation current is now

$$I_s = 3,625 \cdot 10^{-15} \text{ A}$$

(For details see: Thuselt: Physik der Halbleiterbauelemente; Page 141)

Physics of Semiconductor Devices

MatLab-Source for the calculation:

```
%elementary charge
e = 1.60217648*10^-19; % [As]

%doping
N_a = 2*10^15; % [cm^-3]
N_d = 2*10^17; % [cm^-3]
n_i = 1*10^10; % [cm^-3]

% cross-sectional area
A = 10^-4; % [cm^2]

% diffusion constants
D_n = 20; % [cm^2/s]
D_p = 10; % [cm^2/s]
%recombination times
tau_n = 7*10^-7; % [s]
tau_p = 5*10^-7; % [s]

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%Calculating the diffusionlength
L_e = sqrt(D_n*tau_n) % [cm]
L_h = sqrt(D_p*tau_p) % [cm]

%calculating the current-density
J_s = (e*D_n/L_e*(n_i)^2/N_d+e*D_p/L_h*(n_i)^2/N_a) % [A/cm^2]

%calculation the current
I_s = J_s*A % [A]
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